

Shuo Zhang

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Multiphysics Simulation of Crosstalk Effect in Resistive Random Access Memory with Different Metal Oxides. <i>Micromachines</i> , 2022, 13, 266.	2.9	0
2	Rigorous Modeling and Investigation of Low-Field Hole Mobility in Silicon and Germanium Gate-All-Around Nanosheet Transistors. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 4777-4785.	3.0	1
3	Doping engineering to enhance the performance of double-gate pMOSFETs with ultrashort gate length (5Anm). <i>Journal of Computational Electronics</i> , 2021, 20, 1178-1186.	2.5	1
4	Design Considerations for Si- and Ge-Stacked Nanosheet pMOSFETs Based on Quantum Transport Simulations. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 26-32.	3.0	10
5	Modeling and Simulation of Resistive Random Access Memory With Graphene Electrode. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 915-921.	3.0	11
6	An improved multifilamentary conduction model for multiphysics analysis of reset process in resistive random access memory. <i>AIP Advances</i> , 2019, 9, 045310.	1.3	0
7	Performance Comparison Between Si and Ge pDG-FETs for Different Channel Lengths Based on Hole Transport Simulation. , 2019, , .		0
8	Quantum Transport Study of Si Ultrathin-Body Double-Gate pMOSFETs: μ_{eff} and I_{on} vs. V_{gs} and V_{ds} . <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 655-663.	3.0	7
9	Influence of channel length, thickness, and crystal orientation in ultra-scaled double-gate pMOSFETs. , 2017, , .		2